



ZHEJIANG UNIU-NE Technology CO., LTD

浙江宇力微新能源科技有限公司



U3504C Data Sheet

V 1.2

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150V Input, Switching Current Limit Step-Down Converter

General Description

The U3504C is a high voltage, step-down, switching regulator built-in MOSFET. It integrates a high-side, high-voltage, power MOSFET with a current limit of 1A(I_{PK}) typically. The input ranges accommodates a variety of step-down applications, making it ideal for automotive, industry, and lighting applications. Hysteretic voltage-mode control is employed for very fast response. UNI's proprietary feedback control scheme minimizes the number of required external components.

The switching frequency is 150KHZ, allowing for small component size. Thermal shutdown and short-circuit protection (SCP) provide reliable and fault-tolerant operations. Low quiescent current allows the U3504C to be used in battery-powered applications.

The U3504C is available in a ESOP-8 package with an exposed pad.

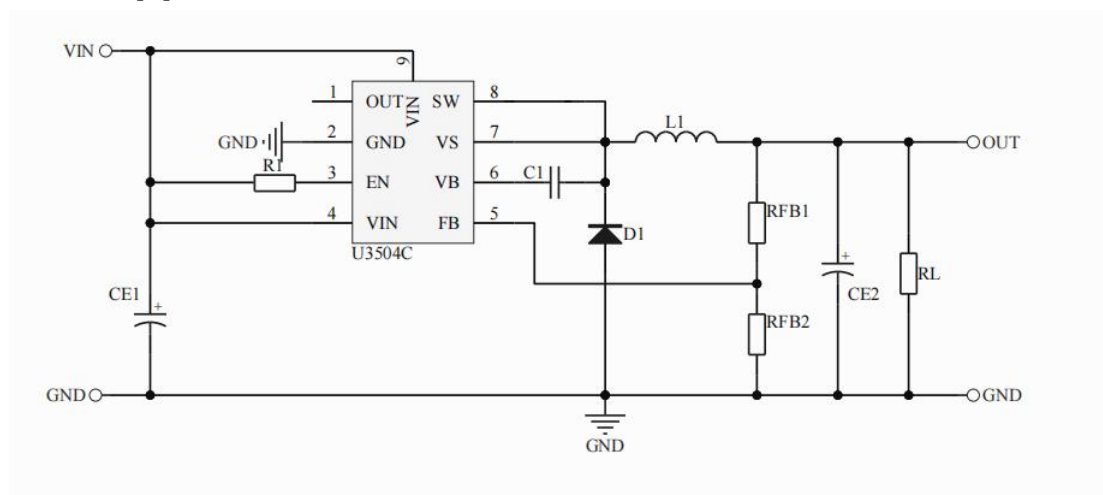
Key Features

- Integrated high voltage start circuit
- Default 5V output (Type)
- Built-In 150V/0.85Ω MOSFET
- Built-in Bootstrap Diode
- Hysteretic Control: No Compensation
- 150KHZ Switching Frequency
- PWM Dimming Control Input for step-down Application
- Short-Circuit Protection (SCP) with Integrated High-Side MOSFET
- Low Quiescent Current
- Thermal Shutdown
- Available in a ESOP-8 Package with an Exposed Pad

Applications

- Scooters, E-Bike Control Power Supplies
- Solar Energy Systems
- Automotive System Power
- Industrial Power Supplies
- High-Power LED Drivers
- USB

Simplified Application



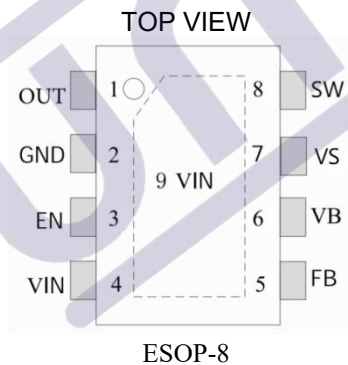
Ordering Information

Part Number	Package	Vo	VIN MAX	MOS IPK	Description
U3504C	ESOP-8	>2V	150V	1A	4000Pcs/Reel

Device Comparison Table

Part Number	Package	Switching Freq(Typ)	MOS	Special Function
U3501C	ESOP-8	150KHZ	60V/20A	LDO 5V
U3502C	ESOP-8	150KHZ	100V/15A	TE PIN
U3504C	ESOP-8	150KHZ	150V/1A	Default 5V output
U3504D	ESOP-8	150KHZ	150V/7A	Default 5V output
U3504E	ESOP-8	150KHZ	150V/10A	Default 5V output
U3507D	DFN5*6-10	150KHZ	150V/10A	/
U3506C	ESOP-8	150KHZ	200V/5A	/

Pin Description



Pin Functions

ESOP-8 Pin #	Name	Description
1	OUT	Default 5V output (Type)
2	GND	Ground. GND
3	EN	En input.Default suspension, built-in resistance
4、9	VIN	Input supply. VIN supplies power to all of the internal control circuitries.
5	FB	Feedback. FB is the input to the voltage hysteretic comparators.
6	VB	VB is the positive power supply for the internal, floating, high-side MOSFET driver. Connect a bypass capacitor between VB and SW.
7	VS	Switch source.Upper drive low potential (Connected to SW Pin)
8	SW	Switch node.

Operation

Hysteresis Voltage Control with Adaptive Threshold Adjustment

The U3504C operates in a hysteretic voltage-control mode to regulate the output voltage. FB is connected to the tap of a resistor divider, which determines the output voltage. The power MOSFET is turned on when the FB voltage (V_{FB}) rises to FBon and remains on until V_{FB} rises to FBoff. The power MOSFET is turned off when V_{FB} drops to FBoff and remains off until V_{FB} falls to FBon. The two thresholds of FBon and FBoff are adjusted adaptively to compensate for all the circuit delays, so the output voltage is regulated with an average 1.275V value at FB.

Floating Driver and Bootstrap Charging

The floating power MOSFET driver is powered by an external bootstrap capacitor.

The bootstrap capacitor is charged and regulated to about 12V by the dedicated internal bootstrap regulator.

If the internal circuit does not have sufficient voltage, and the bootstrap capacitor is not sufficiently charged, extra external circuitry can be used to ensure that the bootstrap voltage is in the normal operating region. Refer to the External Bootstrap Diode section for more details.

Fast charging Function for USB Applications

Because the FB reference of the U3504C is very flexible, it is recommended to use the U3504C for USB Fast charging Applications by connecting the current sense resistor between FB and GND.

Thermal Shutdown

Thermal shutdown is implemented to prevent the chip from operating at exceedingly high temperatures. When the silicon die temperature is higher than its upper threshold, the entire chip shuts down. When the temperature is lower than its lower threshold, the chip is enabled again.

Output Short Protection

The output voltage is well-regulated when V_{FB} is around 1.275V. If the output is pulled low in over-current protection (OCP) or is shorted to GND directly, V_{FB} is low, even though the power MOSFET is turned on. The U3504C regards the low V_{FB} as a failure. The power MOSFET shuts off if the failure time is longer than 10 μ s. The U3504C attempts operation again after a delay of about 300 μ s. The power MOSFET current is also accurately sensed via a current sense MOSFET. If the current is over the current limit, the IC is shut down. This offers extra protection under output-short conditions.

Application Information

Setting the Output Voltage

The output voltage (V_{OUT}) is set by a resistor divider ($R1$ and $R2$) (see the Typical Application on page 1). To achieve good noise immunity and low power loss, $R2$ is recommended to be in the range of $1k\Omega$ to $50k\Omega$. $R1$ can then be determined with Equation (1):

$$R1 = \frac{V_{OUT} - V_{FB}}{V_{FB}} \times R2 \quad (1)$$

Where V_{FB} is 1.275V, typically.

FB has 50K resistance inside, and the calculation is in parallel with $R2$

Output Capacitor and Frequency Setting

The output capacitor (C_{OUT}) is necessary for achieving a smooth output voltage. The ESR of the capacitor should be sufficiently large compared to the capacitance; otherwise, the system may behave in an unexpected way, and the current ripple may be very high when the power MOSFET switches on. V_{FB} becomes 1.275V. To charge the capacitor and generate 1.275V at FB, the system needs ESR and some inductor current. For example, for a 5V V_{OUT} , if the forward capacitor is $0.1\mu F$, the suggested ESR range of the output capacitor is $100m\Omega$ to $250m\Omega$. Tantalum or aluminum electrolytic capacitors with a small ceramic capacitor are recommended.

A forward capacitor across $R1$ is recommended when the output capacitor is tantalum or aluminum electrolytic, which can set the desired frequency if the output capacitor and ESR cannot be changed. The forward capacitor can reduce the output voltage ripple.

In some application, simply a forward capacitor may not get proper frequency, then we can add a forward resistor in series with the forward capacitor or even more add a ceramic on the output.

Selecting the Inductor

The inductor (L) is required to convert the switching voltage to a smooth current to the load. Although the output current is low, it is recommended that the inductor current be continuous in each switching period to prevent reaching the current limit. Calculate the inductor value with Equation (2):

$$L = \frac{(V_{IN} - V_{OUT}) \times V_{OUT}}{F_{SW} \times I_{OUT} \times V_{IN} \times K} \quad (2)$$

Where K is a coefficient of about 0.15 ~ 0.85

Output Rectifier Diode

The output rectifier diode supplies current to the inductor when the high-side switch is off. To reduce losses due to the diode forward voltage and recovery times, use a Schottky diode. The average current through the diode can be approximated with Equation (3):

$$I_D = I_{OUT} \times \left(1 - \frac{V_{OUT}}{V_{IN}}\right) \quad (3)$$

Choose a diode with a maximum reverse voltage rating greater than the maximum input voltage and a current rating is greater than the average diode current.

Input Capacitor (C_{IN})

The input current to the step-down converter is discontinuous and therefore requires a capacitor to supply AC current to the step-down converter while maintaining the DC input voltage. Use low ESR capacitors for the best performance, especially under high switching frequency applications.

The RMS current through the input capacitor can be calculated with Equation (4):

$$I_{IN_AC} = I_{OUT} \times \sqrt{\frac{V_{OUT}}{V_{IN}} \times \left(1 - \frac{V_{OUT}}{V_{IN}}\right)} \quad (4)$$

With low ESR capacitors, the input voltage ripple can be estimated with Equation (5):

$$\Delta V_{IN} = \frac{I_{OUT} \times V_{OUT}}{F_{SW} \times C_{IN} \times V_{IN}} \times \left(1 - \frac{V_{OUT}}{V_{IN}}\right) \quad (5)$$

Choose an input capacitor with enough RMS current rating and enough capacitance for small input voltage ripples.

When electrolytic or tantalum capacitors are applied, a small, high-quality ceramic capacitor (i.e.: 0.1 μ F) should be placed as close to the IC as possible.

External Bootstrap Diode

An external bootstrap diode may enhance the efficiency of the converter (see Figure 2).

The bootstrap diode can be a low-cost one, Optimize circuit structure, save cost, and reduce error rate for peripheral circuit configuration.

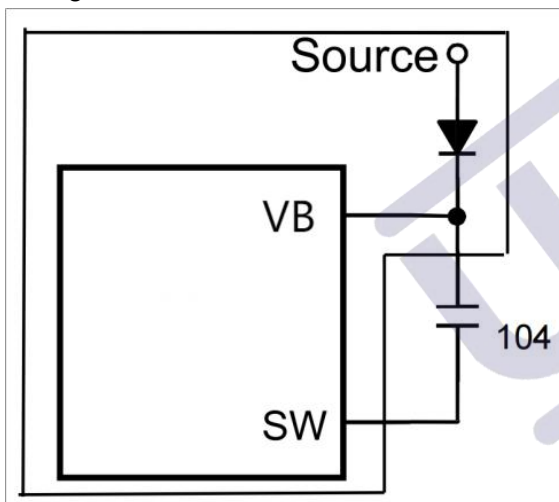


Figure 2: External Bootstrap Diode

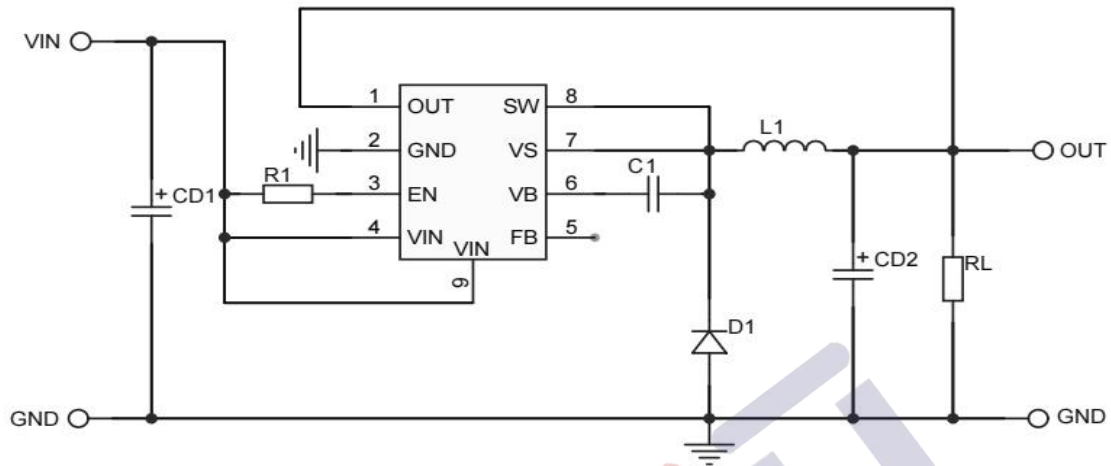
PCB Layout Guidelines

Efficient PCB layout is critical for stable operation. For best results, follow the guidelines below.

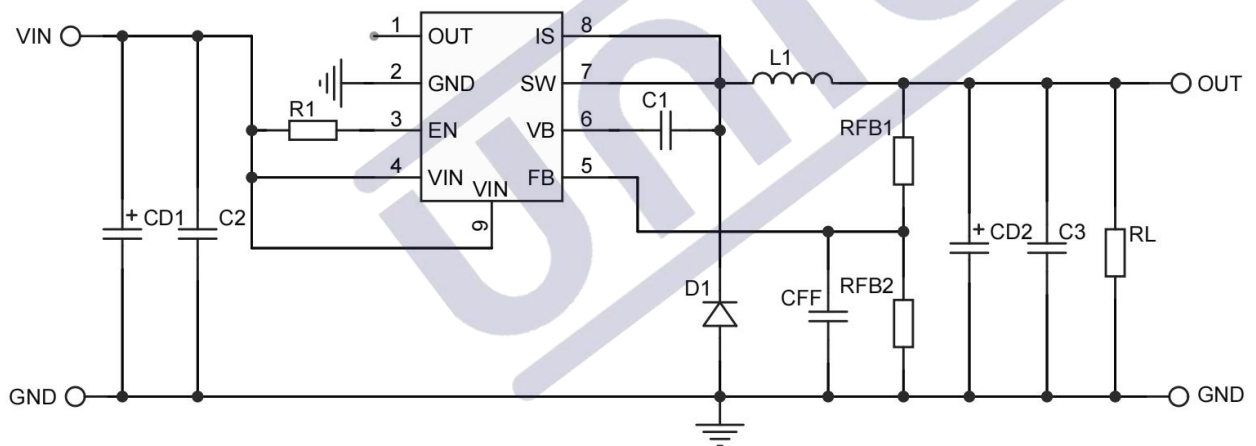
1. Place the input decoupling capacitor, catch diode, and the U3504C (VIN, SW, and PGND) as close to each other as possible.
2. Keep the power traces very short and fairly wide, especially for the SW node. This can help greatly reduce voltage spikes on the SW node and lower the EMI noise level.
3. Run the feedback trace as far from the inductor and noisy power traces (like the SW node) as possible.
4. Place thermal vias with 15mil barrel diameter and 40mil pitch (distance between the centers) under the exposed pad

Typical Application Circuit

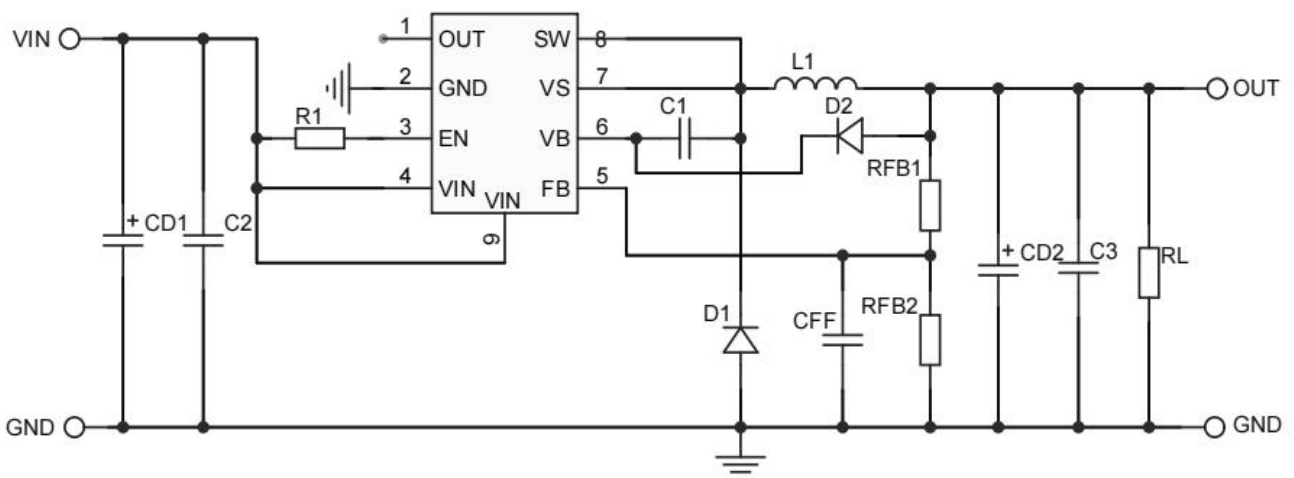
APP1: $V_{OUT}=5V$



APP1: $V_{OUT}<10V$



APP2: $V_{OUT}=10\sim15V$



[illegible][illegible]

- Uthmaniyah

1、版本记录

DATE	REV.	DESCRIPTION
2023/7/25	1.0	首次发布
2024/5/12	1.1	优化参数
2024/7/22	1.2	增加功能比较表和部分参数修改

2、免责声明

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